SKML2803

SOT-23 Plastic-Encapsulate Transistors

MOSFET(N-Channel)

FEATURES
TrenchFET Power MOSFET

SOT-23

1. GATE
2. SOURCE
3. DRAIN

MAXIMUM RATINGS (TA=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{DS}	Drain-Source voltage	30	V
V_{GS}	Gate-Source voltage	± 20	V
I_D	Drain current	4.5	A
P_D	Power Dissipation	1.13	W
Tj	Junction Temperature	150	℃
Tstg	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

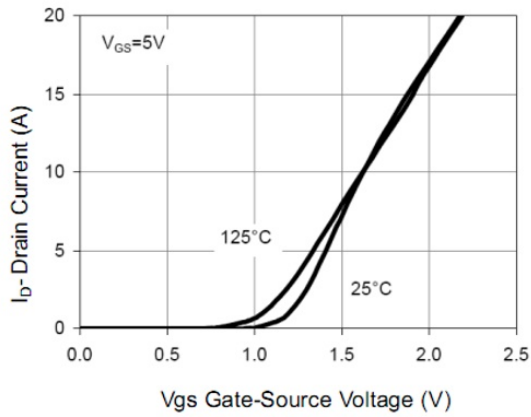| Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=250uA	30			V
Gate-Threshold Voltage	$V_{th(GS)}$	V_{DS}= V_{GS}, I_D=250 uA	1	1.4	3	V
Gate-body Leakage	I_{GSS}	V_{DS}=0V, V_{GS}=± 20V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	uA
Drain-Source On-Resistance	$r_{DS(ON)}$	V_{GS}=10 V, I_D=4.9A		31	42	m Ω
		V_{GS}=4.5V, I_D=4.1A		46	65	m Ω
Forward Trans conductance	gfs	V_{DS}=5V, I_D=2.0A		9.5		s
Dynamic Characteristics						
Input Capacitance	Ciss	V_{DS}=15V, V_{GS}=0V, f=200K Hz		234.85		pF
Output Capacitance	Coss			33.70		
Reverse Transfer Capacitance	Crss			26.82		
Switching Capacitance						
Turn-on Delay Time	td(on)	V_{DD}=15V, I_D=1.0A, V_{GEN}=10 V R_{GEN}=6 Ω		4.26		nS
Turn-on Rise Time	tr			2.83		nS
Turn-off Delay Time	td(off)			18.72		nS
Turn-off Fall Time	tf			2.59		nS
Total Gate Charge	Qg	V_{DS}=15V, I_D=4.5A, V_{GS}=10V ,		4.02		nC
Gate-Source Charge	Qgs			1.18		nC
Gate-Drain Charge	Qgd			0.86		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage	V_{SD}	V_{GS}=0V, Is=2.0A			1.2	V
Diode Forward Current	Is				1.7	A

Typical Characteristics

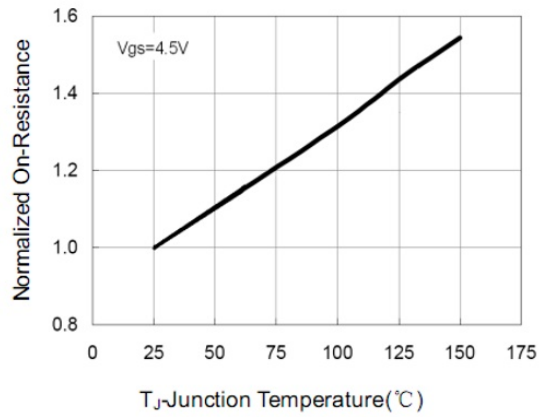**Figure 1 Transfer Characteristics**

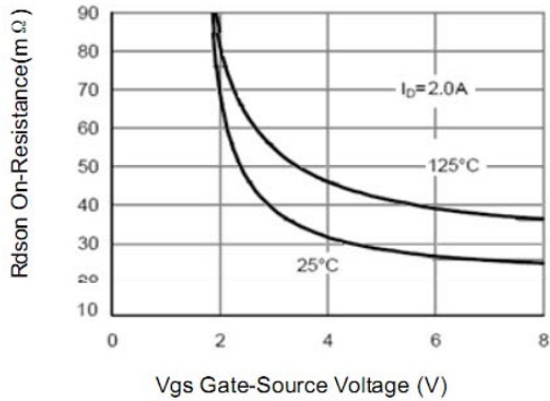

Figure 2 Drain-Source On-Resistance
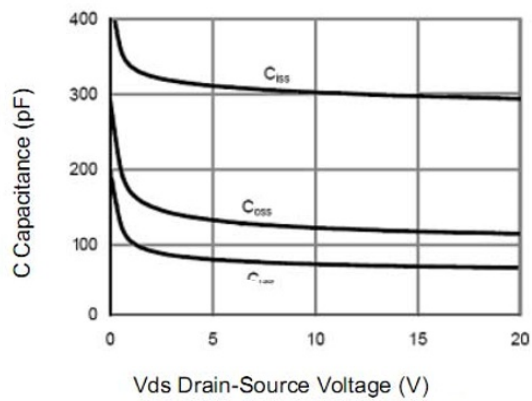

Figure 3 Rdson vs Vgs
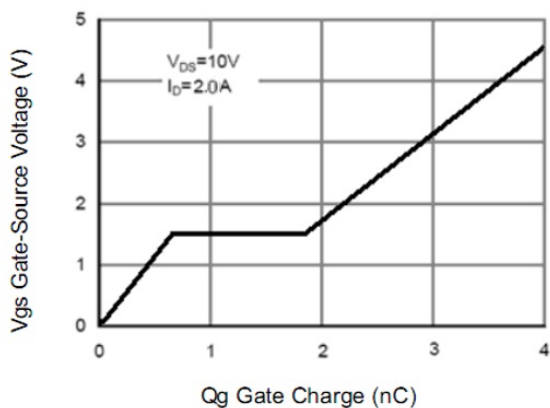

Figure 4 Capacitance vs Vds
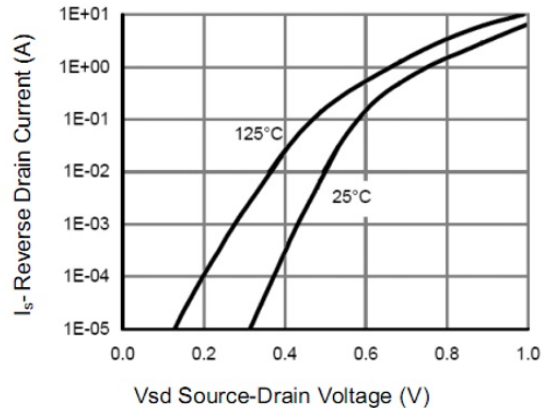

Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward

单击下面可查看定价，库存，交付和生命周期等信息

>>SHIKUES(时科)